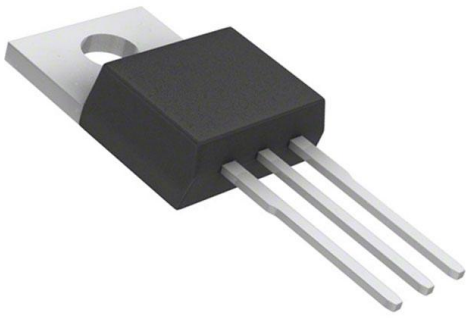


FJP52000TU Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	FJP52000TU-DG
Manufacturer	onsemi
Manufacturer Product Number	FJP52000TU
Description	TRANS NPN 250V 17A TO220-3
Detailed Description	Bipolar (BJT) Transistor NPN 250 V 17 A 30MHz 80 W Through Hole TO-220-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

FJP52000TU

Series:

-

Transistor Type:

NPN

Voltage - Collector Emitter Breakdown (Max):

250 V

Current - Collector Cutoff (Max):

5 μ A (ICBO)

Power - Max:

80 W

Operating Temperature:

-50°C ~ 150°C (TJ)

Package / Case:

TO-220-3

Base Product Number:

FJP520

Manufacturer:

onsemi

Product Status:

Obsolete

Current - Collector (Ic) (Max):

17 A

Vce Saturation (Max) @ Ib, Ic:

3V @ 800mA, 8A

DC Current Gain (hFE) (Min) @ Ic, Vce:

80 @ 1A, 5V

Frequency - Transition:

30MHz

Mounting Type:

Through Hole

Supplier Device Package:

TO-220-3

Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0075

FJP5200

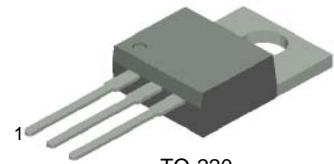
NPN Epitaxial Silicon Transistor

Applications

- High-Fidelity Audio Output Amplifier
- General Purpose Power Amplifier

Features

- High Current Capability: $I_C = 17A$.
- High Power Dissipation : 80watts.
- High Frequency : 30MHz.
- High Voltage : $V_{CEO}=250V$
- Wide S.O.A for reliable operation.
- Excellent Gain Linearity for low THD.
- Complement to FJP1943
- Thermal and electrical Spice models are available.
- Same transistor is also available in:
 - TO264 package, 2SC5200/FJL4315 : 150 watts
 - TO3P package, 2SC5242/FJA4313 : 130 watts
 - TO220F package, FJPF5200 : 50 watts



TO-220
1.Base 2.Collector 3.Emitter

Absolute Maximum Ratings* $T_a = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
BV_{CBO}	Collector-Base Voltage	250	V
BV_{CEO}	Collector-Emitter Voltage	250	V
BV_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current(DC)	17	A
I_B	Base Current	1.5	A
P_D	Total Device Dissipation($T_C=25^\circ C$) Derate above $25^\circ C$	80 0.64	W W/ $^\circ C$
T_J, T_{STG}	Junction and Storage Temperature	- 50 ~ +150	$^\circ C$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics* $T_a=25^\circ C$ unless otherwise noted

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.25	$^\circ C/W$

* Device mounted on minimum pad size

h_{FE} Classification

Classification	R	O
h_{FE1}	55 ~ 110	80 ~ 160

Electrical Characteristics* $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C=5\text{mA}, I_E=0$	250			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}, R_{BE}=\infty$	250			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E=5\text{mA}, I_C=0$	5			V
I_{CBO}	Collector Cut-off Current	$V_{CB}=230\text{V}, I_E=0$			5.0	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB}=5\text{V}, I_C=0$			5.0	μA
h_{FE1}	DC Current Gain	$V_{CE}=5\text{V}, I_C=1\text{A}$	55		160	
h_{FE2}	DC Current Gain	$V_{CE}=5\text{V}, I_C=7\text{A}$	35	60		
$V_{CE}(\text{sat})$	Collector-Emitter Saturation Voltage	$I_C=8\text{A}, I_B=0.8\text{A}$		0.4	3.0	V
$V_{BE}(\text{on})$	Base-Emitter On Voltage	$V_{CE}=5\text{V}, I_C=7\text{A}$		1.0	1.5	V
f_T	Current Gain Bandwidth Product	$V_{CE}=5\text{V}, I_C=1\text{A}$		30		MHz
C_{ob}	Output Capacitance	$V_{CB}=10\text{V}, f=1\text{MHz}$		200		pF

* Pulse Test: Pulse Width=20 μs , Duty Cycle \leq 2%**Ordering Information**

Part Number	Marking	Package	Packing Method	Remarks
FJP5200RTU	J5200R	TO-220	TUBE	hFE1 R grade
FJP5200OTU	J5200O	TO-220	TUBE	hFE1 O grade

Typical Characteristics

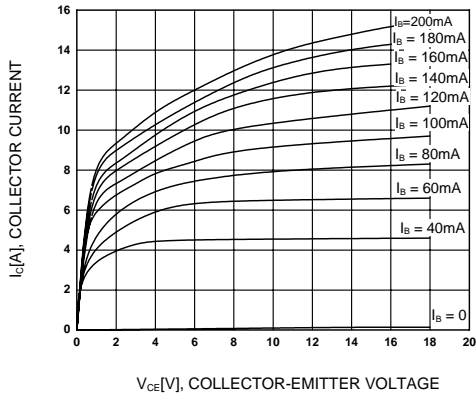


Figure 1. Static Characteristic

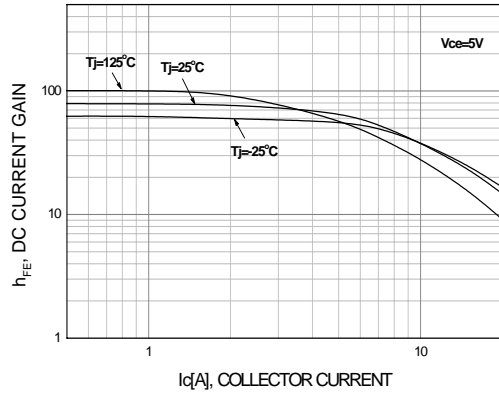


Figure 2. DC current Gain (R grade)

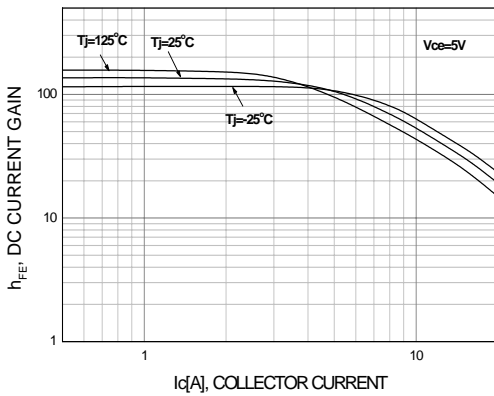


Figure 3. DC current Gain (O grade)

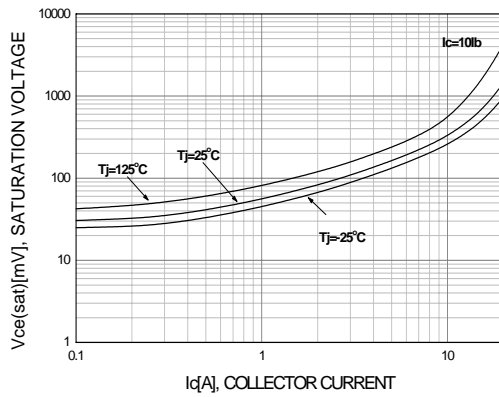


Figure 4. Collector-Emitter Saturation Voltage

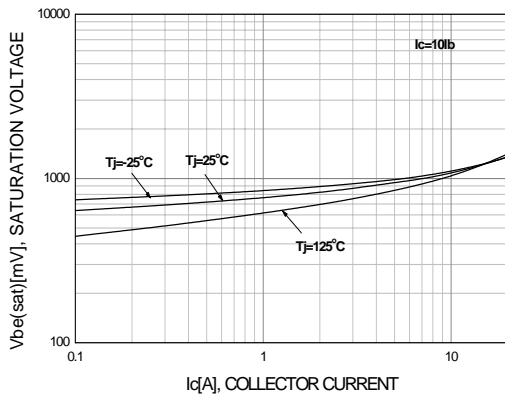


Figure 5. Base-Emitter Saturation Voltage

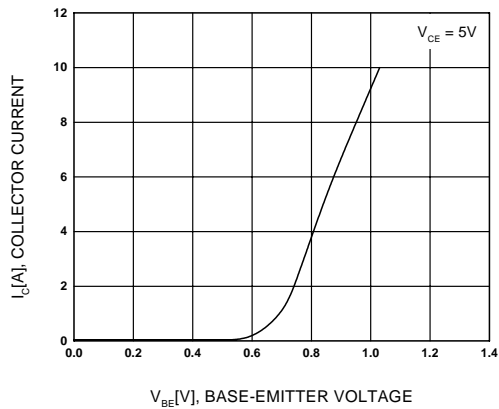


Figure 6. Base-Emitter On Voltage

Typical Characteristics

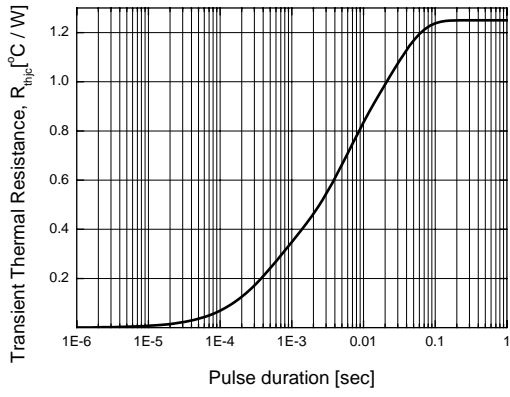


Figure 7. Thermal Resistance

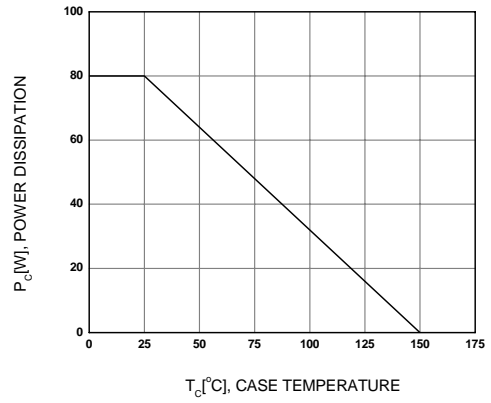
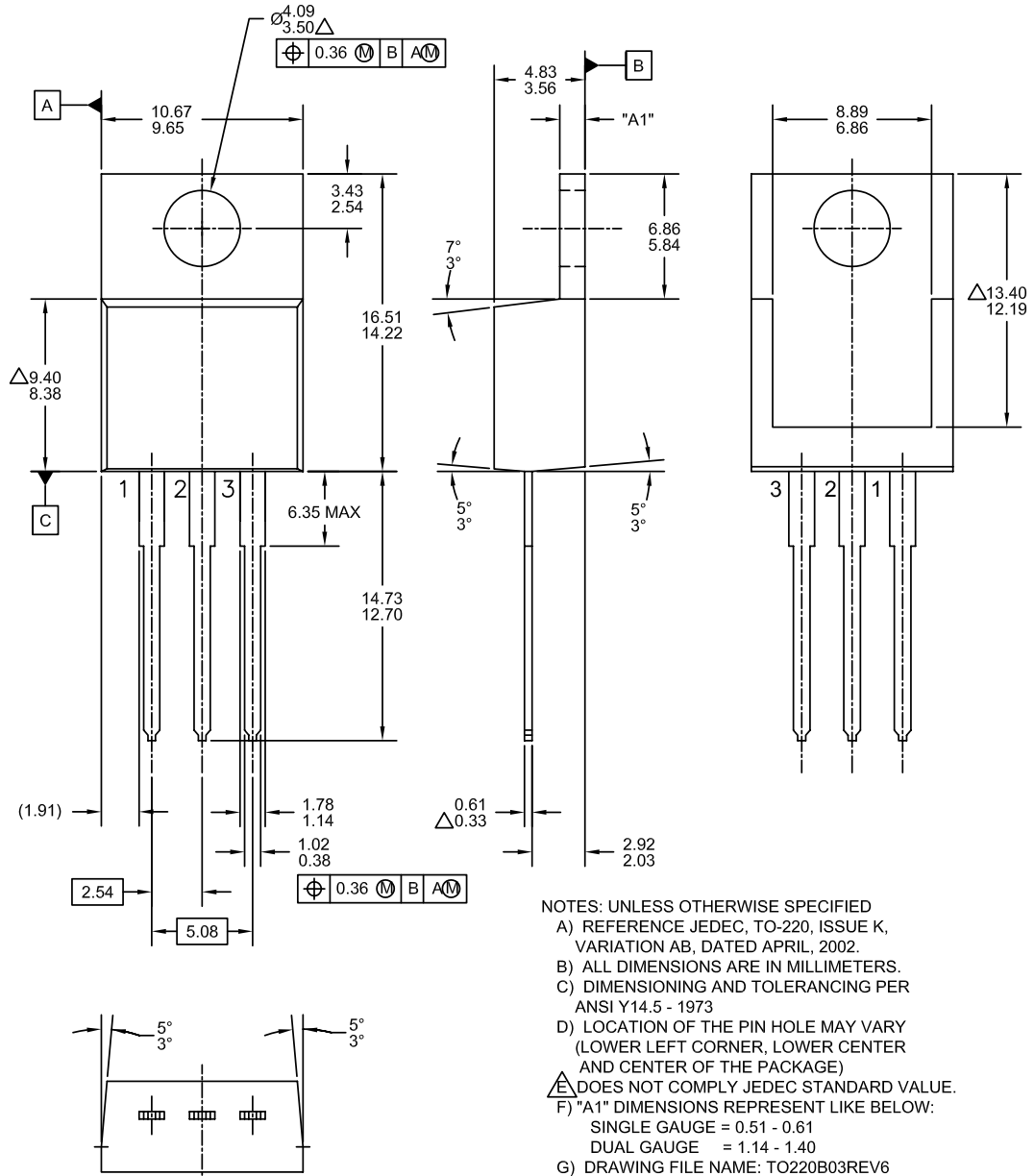


Figure 8. Power Derating

Mechanical Dimensions

TO220





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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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